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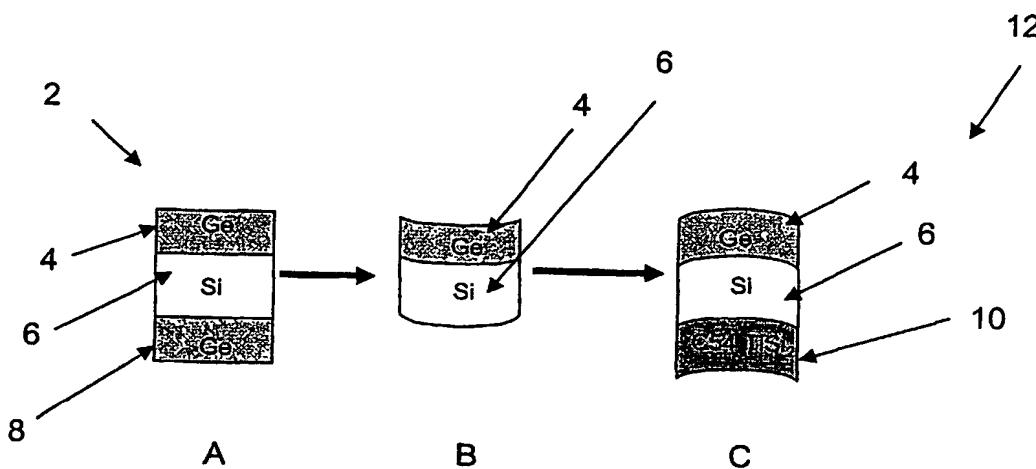
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(54) Title: METHOD AND STRUCTURE OF STRAIN CONTROL OF SiGe BASED PHOTODETECTORS AND MODULATORS



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(57) Abstract: A SiGe or Ge structure comprises a substrate and a SiGe or Ge layer that is formed on a first surface of the substrate. A silicidation or germanide layer is formed on a second surface of the substrate so to increase the tensile strain of the SiGe or Ge layer on the first surface.

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